60V P-Channel MOSFETs

General Description

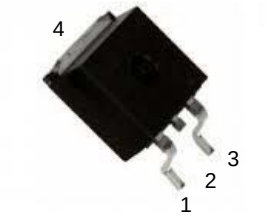
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-60V	27mΩ	-42A

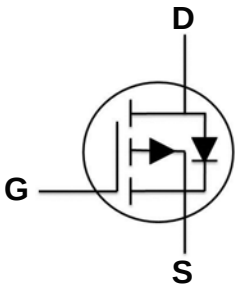
Features

- *-60V,-42A, RDS(ON) =27mΩ@VGS = -10V*
- *Fast switching*
- *Green Device Available*
- *Suit for -4.5V Gate Drive Applications*

TO-263 Pin Configuration



1. Gate
2. Drain
3. Source
4. Drain



Applications

- *POL Applications*
- *Load Switch*
- *LED Application*

Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	-42	A
	Drain Current – Continuous (T_C=100℃)	-26.5	A
I_{DM}	Drain Current – Pulsed[1]	-168	A
EAS	Single Pulse Avalanche Energy[2]	105	mJ
IAS	Single Pulse Avalanche Current[2]	46	A
P_D	Power Dissipation (T_C=25℃)	121	W
	Power Dissipation – Derate above 25℃	0.97	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.03	℃/W

60V P-Channel MOSFETs

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-60V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-48V , V_{GS}=0V , T_J=125℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-8A	---	22	27	mΩ
		V_{GS}=-4.5V , I_D=-6A	---	28	36	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.6	-2.5	V
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-3A	---	18	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=-30V , V_{GS}=-10V , I_D=-5A	---	43.8	88	nC
Q_{gs}	Gate-Source Charge[3,4]		---	4.6	9	
Q_{gd}	Gate-Drain Charge[3,4]		---	8.3	17	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=-30V , V_{GS}=-10V , R_G=6Ω I_D=-1A	---	25	50	ns
T_r	Rise Time[3,4]		---	13.8	28	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	148	290	
T_f	Fall Time[3,4]		---	51	100	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , F=1MHz	---	2595	3900	pF
C_{oss}	Output Capacitance		---	162	240	
C_{rss}	Reverse Transfer Capacitance		---	115	170	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-42	A
I_{SM}	Pulsed Source Current		---	---	-70	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	-1	V
T_{rr}	Reverse Recovery Time	VR=30V,IS=10A di/dt=100A/us TJ=25℃	---	150	---	nS
Q_{rr}	Reverse Recovery Charge		---	380	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=46A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

60V P-Channel MOSFETs

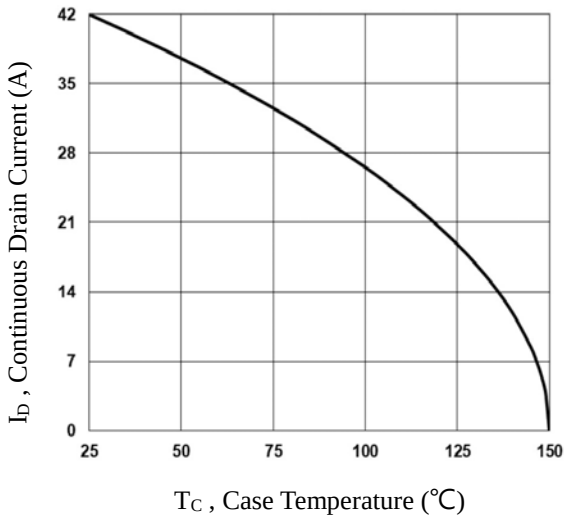


Fig.1 Continuous Drain Current vs. T_C

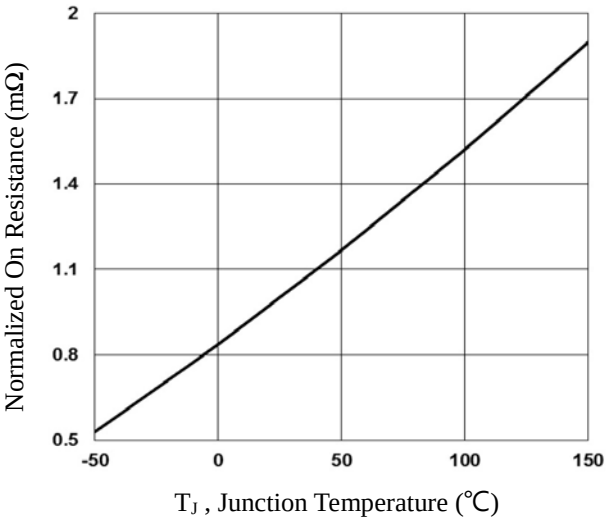


Fig.2 Normalized RDSON vs. T_J

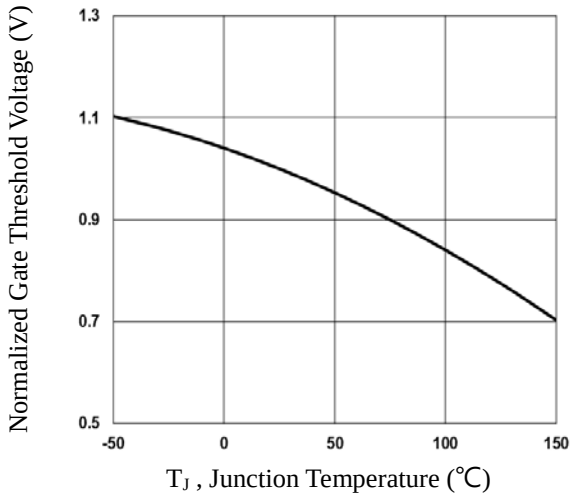


Fig.3 Normalized Vth vs. T_J

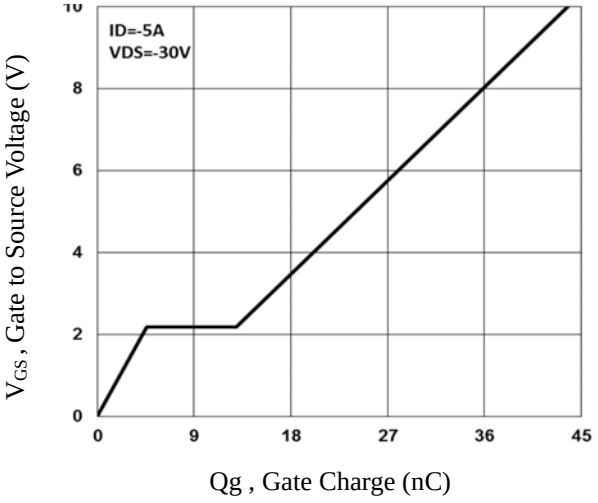


Fig.4 Gate Charge Characteristics

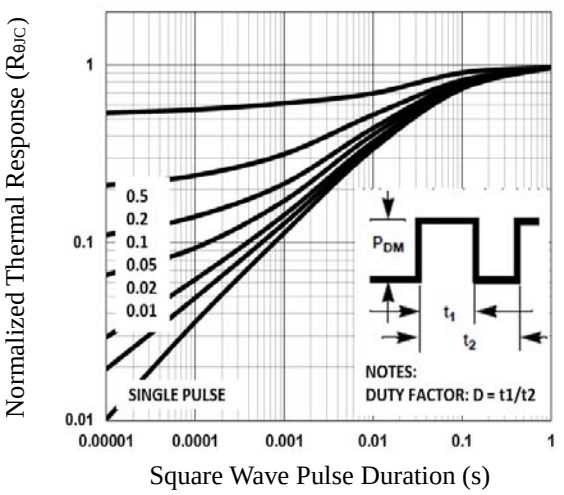


Fig.5 Normalized Transient Impedance

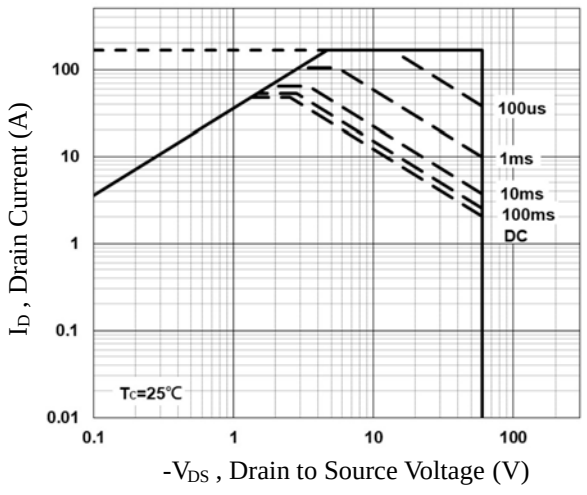


Fig.6 Maximum Safe Operation Area

60V P-Channel MOSFETs

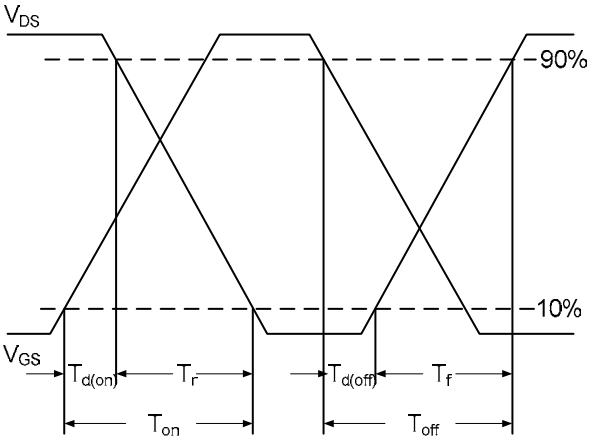


Fig.7 Switching Time Waveform

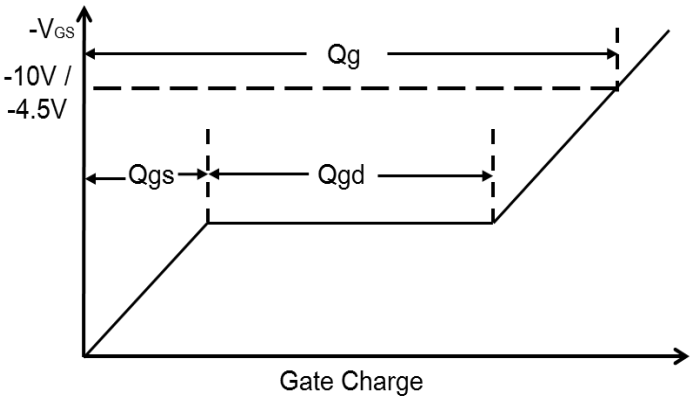


Fig.8 Gate Charge Waveform

60V P-Channel MOSFETs

TO-263 PACKAGE INFORMATION